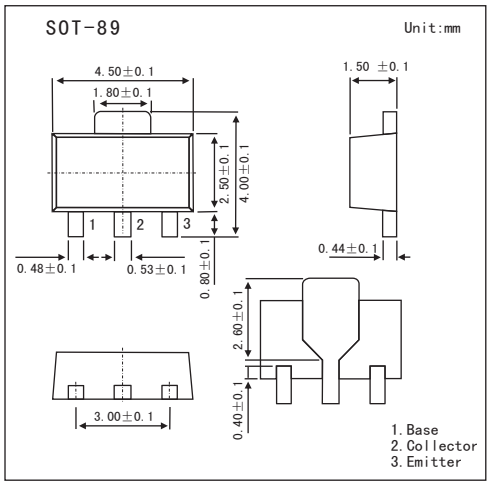
Silicon NPN Triple Diffused

2SC3380



Features

High frequency high voltage amplifier

High voltage switch

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	300	V
Collector-emitter voltage	V_{CEO}	300	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Total power dissipation	P_C*	1	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* Value on the alumina ceramic board (12.5 × 20 × 0.7 mm)

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	I_C = 10 μA, I_E = 0	300			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 1 mA, I_B = 0	300			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	I_E = 10 μA, I_C = 0	5			V
Collector cutoff current	I_{CEO}	V_{CB} = 250V,I_B=0			1.0	μA
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = 20 mA, I_B = 2 mA			1.5	V
DC current gain	h_{FE}	V_{CE} =20V,Ic=20mA	30		200	
Transition frequency	f_T	V_{CE} = 20V ,Ic=20mA		80		MHz
Output Capacitance	C_{ob}	V_{CB} = 20 V, I_E = 0, f = 1.0 MHz			4	pF

Marking

Marking	AS